高性能反射防止膜"メソアモルファスコート"用 超低屈折率多孔質シリカ薄膜の作製

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Fabrication of a Porous SiO₂ Thin Film with an Ultralow Refractive Index for High Performance Anti-reflective Coatings "Meso Amorphous Coat"†

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光学機器を製造・販売しているニコンにおいて,反射防止膜は透過率向上や迷光の抑制のために欠かせない重要な技 術である.工業的に広く用いられている多層反射防止膜のなかでも,最上層の低屈折率化はその性能向上に最も大きな 影響を与える.低屈折率層には空気を含む多孔質構造が求められるが,光の散乱を防ぐためにはその構造は微細なもの でなくてはならない.本稿では簡便なゾル - ゲル法を用いた多層反射防止膜の最上層用の低屈折率薄膜の作製について 説明する.反応に用いる原料に適切な分子構造の溶媒と高い塩基性を有する塩基触媒を選択することにより,微細な多 孔質構造を有する屈折率1.17の多孔質シリカ薄膜を作製することに成功した.膜構造の観察とシミュレーションにより, 低散乱および超低屈折率の形成要因を明らかにした.さらに,作製した膜に疎水性官能基を導入することにより空気中 の水分の吸着による屈折率変化を低減した. この薄膜は"メソアモルファスコート"の最上層としてカメラレンズに搭 載されている.

Anti-reflective coatings are a key technology in Nikon Corporation, which manufactures optical equipment, for improving transmittance and reducing stray light. A lower refractive index of the top layer in the multilayer antireflective coatings, which is widely used in industry, has the greatest effect on improving its performance. The top layer must have a porous structure containing air, but the structure must be fine to prevent light scattering. This paper describes a simple sol-gel method for fabricating a thin film with a low refractive index for the top layer of a multilayer anti-reflective coating. By selecting solvent with appropriate molecular structures and base catalyst with high basicity as raw materials for the reaction, porous $SiO₂$ thin films with a refractive index of 1.17 and a fine porous structure were successfully fabricated. Observation of the film structure and simulation revealed the formation process of low scattering and ultra-low refractive index. Furthermore, by introducing hydrophobic functional groups into the fabricated films, the variation of refractive index due to the adsorption of moisture in the air was reduced. This thin film is applied to camera lenses as the top layer of "Meso Amorphous Coat".

Key words 反射防止膜,低屈折率膜,光学薄膜,多孔質シリカ,ゾル - ゲル法 anti-reflective coating, low refractive index film, optical thin film, porous silica, sol-gel method

1 Introduction

Anti-reflective (AR) coatings are used in various optical products, such as cameras, microscopes, and display panels [1]-[3]. A multilayer AR coating comprises several stacked layers with varying refractive indices [4]. Among these layers, the top layer contributes the most to AR performance. Decreasing the refractive index (n) of the top layer is necessary to improve AR performance. MgF_2 has the lowest refractive index $(n = 1, 38)$ but is not sufficiently low for AR coatings [5].

Most low refractive index materials possess a porous structure. The total refractive index of an AR film can be reduced by forming pores containing air $(n = 1)$ in the film. To date, various porous materials, such as $CaF₂$, $MgF₂$, and Al_2O_3 have been synthesized [6] – [8]. In particular, SiO₂ was

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focused on materials for preparing porous structures [9] – [11]. The use of large amount of air to decrease the refractive index of a film tends to cause considerable scattering of light [12], [13]. Moreover, these materials have unstable refractive indices because their pores adsorb moisture from the air easily [14]. To prevent the adsorption of moisture, hydrophilic Si-OH groups of the film surface are often capped. However, the refractive index of the film increases unless the amount of capping agent is controlled [15], [16].

Many studies have reported that a multi-coating of a porous film that contains $SiO₂$ and whose refractive index is lesser than 1.20 can achieve high transmittance [17], [18]. Therefore, a thin film with $n < 1.20$ is required for AR coating. However, porous $SiO₂$ thin films prepared via sol-gel reactions often contain large $SiO₂$ particles (several tens of nanometers) in their inner structure and exhibit large Rayleigh scattering, which decreases the transmittance of the film [5], [19], [20]. Therefore, a finely structured thin film of porous $SiO₂$ is required for optical applications. In this study, an easy sol-gel method was used to prepare porous $SiO₂$ thin films. The obtained porous $SiO₂$ films exhibited low light scattering and were humidity resistant. In addition, structural analysis and calculations were conducted, and the factors responsible for the low refractive index and scattering were discussed.

2 Experiment

2.**1**. **Materials**

Tetramethyl orthosilicate (TMOS; Tokyo Chemical Industry Co., Ltd., Tokyo, Japan) was used as the silica source. 1-Methoxy-2-propanol (PGME; FUJIFILM Wako Pure Chemical Corporation, Osaka, Japan) was used as a solvent. Triethylamine (TEA; Tokyo Chemical Industry Co., Ltd., Tokyo, Japan) was used as the catalyst for the sol-gel reaction. Hexamethyldisilazane (HMDS; Tokyo Chemical Industry Co., Ltd., Tokyo, Japan) was used for the surface treatment of the porous $SiO₂$ thin films.

2.**2**. **Sample Preparation**

The typical preparation methods are described in this section. First, PGME (54.43 g) was poured into a polytetrafluoroethylene (PTFE) bottle. H2O (1.731 *μ*L), TEA (36.10 *μ*L), and TMOS (7.310 g) were then added into the bottle at a molar ratio of TMOS : H_2O : TEA = $1:2:0.01$ and stirred for ~27 h at the room temperature. The as-prepared coating liquid containing 4.54 wt% of $SiO₂$ was filtered using a PTFE filter having a pore size of $5.0 \mu m$ and then spin-coated onto a substrate. The films thus obtained were heated to 160°C for 3 h to obtain a film denoted as $SiO₂$ PGME_TEA. After heating, the $SiO₂$ PGME TEA was treated with HMDS to enhance its hydrophobicity. Subsequently, the film, which was coated on a substrate with 30 mm diameter, was sealed in a closed vessel with HMDS (0.6135 *μ*L) for 24 h at room temperature. Finally, the product was heated at 60 ºC for 0.5 h to form SiO₂ HMDS.

3 Results and Discussions

3.**1**. **Effect of Solvent on SiO2 Thin Films**

The relationship between the sol-gel reaction time and the refractive index of the films was investigated. In addition, the experiment was repeated with different solvents namely, PGME, methanol, 1-propanol, and 1-pentanol, to investigate the effect of a solvent on the relationship. Figure 1 shows the relationship between the sol-gel reaction time and the refractive index of the prepared films. In all cases, the refractive index decreased with reaction time. This behavior was consistent with previously reported results [21]. The behavior is attributed to generating a bulky structure that consists of $SiO₂$ and enlarges over time in the reaction mixture. The bulkier the $SiO₂$ structure, the more the number of and larger pores, formed that contain air. Therefore, the refractive index of the thin films decreases over time. The largest decrease in the refractive index was observed when 1-pentanol was used as a solvent. The refractive indices of the thin films prepared using methanol and 1-propanol were almost equal $(n \sim 1.20)$.

Fig. 1Relationship between the sol-gel reaction time and the refractive index of thin films prepared with (a) PGME, (b) methanol, (c) 1-propanol, and (d) 1-pentanol as solvents

Figure 2 shows the relationship between refractive index of the film prepared from the coating liquid reacted for an arbitrary time and transmittance at 350 nm of the same coating liquid for different solvents. In all cases, the transmittance and refractive index decreased with reaction time simultaneously. As shown in Fig. 1, $SiO₂$ structures grew and aggregated in coating liquid during the sol-gel reaction, which increased the porosity of the $SiO₂$ thin films. Figure 2 provides data to consider how $SiO₂$ fine structure can be formed without particle growth and aggregation, increasing scattering and decreases transmittance. The transmittance corresponding to PGME was higher than that corresponding to methanol and 1-propanol when the refractive indices of the thin films were almost the same; for example, the refractive index was approximately 1.20. The reaction mixture containing 1-pentanol exhibits the highest transmittance. These results indicate that finely structured $SiO₂$ was formed when PGME and 1-pentanol were used as solvents.

Fig. 2Relationship between refractive index of the thin film and the corresponding transmittance at 350 nm of the same coating liquid prepared using (a) PGME, (b) methanol, (c) 1-propanol, and (d) 1-pentanol

The results showed transesterification occurred between the methoxy group of TMOS and the solvent during the solgel reaction. The reactivity of silanes that underwent transesterification was lower than that of TMOS, possibly because silanes contain a bulkier alkoxy group than TMOS. The bulky alkoxy group on the surface of the $SiO₂$ structure prevented the aggregation of the $SiO₂$ particles. The transesterification reaction also prevented the growth and aggregation of $SiO₂$ structures. In addition, PGME is considered a suitable solvent for controlling the refractive index of AR coatings because it tends to reduce the refractive index near

1.20 gradually.

Figure 3 shows the photographs and optical microscopic images of the thin films prepared in this study. As shown in Fig. 3a-b, radial striations can be observed in the $SiO₂$ thin film surface prepared using methanol. In contrast, thin films prepared using 1-propanol (Fig. 3c-d), 1-pentanol (Fig. 3e-f), and PGME (Fig. 3g-h) exhibit smooth surfaces.

Fig. 3Appearance of a thin film prepared using a coating liquid containing (a) methanol, (c) 1-propanol, (e) 1-pentanol, and (g) PGME; (b), (d), (f), and (h) represent the corresponding optical microscopic images. (Scale bar in b, d, f, and h represents 200 μm.)

From the above results, PGME can be considered a suitable solvent for fabricating porous silica thin films as AR coating from view points of control of refractive index and appearance.

3.**2**. **Effect of the Base on the Structure of Porous SiO2 Thin Films**

To investigate the effect of the base on the structure of $SiO₂$ thin films, $SiO₂$ thin films were prepared using NH₃, propylamine (PA), and diethylamino (DEA) in place of TEA in the original preparation method. In each experiment, the refractive index of the thin films was adjusted to $n = 1.17$ by controlling the reaction time.

Figure 4 shows the cross-sectional SEM images of the thin films. A $SiO₂$ framework comprising small connected particles was observed in all porous $SiO₂$ thin films. In Fig. 4, the diameter of a $SiO₂$ primary particle was considered corresponding to the thickness of the framework. Therefore, the $SiO₂$ primary particle diameter was measured at four points and averaged in each SEM image. $SiO₂$ PGME_NH₃ (Fig. 4a) and $SiO₂$ PGME PA (Fig. 4b) possessed thick frameworks. The second thinnest and thinnest frameworks were observed in SiO_2 PGME DEA (Fig. 4c) and SiO_2 PGME_TEA (Fig. 4d), respectively. The thicknesses of the $SiO₂$ PGME_NH₃, $SiO₂$ PGME_PA, $SiO₂$ PGME_DEA, and SiO2_PGME_TEA frameworks, measured using their SEM images, were 15.8 nm, 15.3 nm, 11.0 nm, and 9.8 nm, respectively.

Fig. 4 Cross-sectional SEM images of (a) $SiO₂$ PGME NH₃, (b) $SiO₂$ PGME PA, (c) $SiO₂$ PGME DEA, and (d) $SiO₂$ PGME_TEA

Table 1 shows the amount of scattered light at 350 nm by thin films. The amount of light scattered by $SiO₂$ -PGME_PA was the highest, whereas that scattered by $SiO₂$ -PGME_ TEA was the smallest.

Figure 5 shows the viscosity of the reaction mixture to reaction time. The viscosity increased with reaction time for samples prepared using PA, DEA, and TEA catalysts. Nota-

Table 1 Amount of scattered light at 350 nm by the porous $SiO₂$ thin films

| | Amount of scattering at 350 nm/ppm |
|-----------------------------|------------------------------------|
| $SiO2$ PGME NH ₃ | 248 |
| SiO ₂ PGME PA | 388 |
| $SiO2$ PGME DEA | 265 |
| SiO ₂ PGME TEA | 204 |

bly, the maximum increase in viscosity is observed for TEA. The type of basic catalyst affected the formation of $SiO₂$ because of the inductive effect, steric hindrance of the catalysts and solvent [22]. The pKa values of NH3, propylamine, diethylamine and triethylamine in water are 9.21, 10.53, 10.98 and 10.65, respectively [23]. It means that basicity decreases in the order diethylamine > triethylamine > propyl- $\text{amine} > \text{NH}_3$. However, the pKa values listed here are those in water, which have been widely reported, and these values vary with the solvent. It has been reported that tertiary amines may have a higher pKa than secondary amines in organic solvents [24]. This is owing to the stability of the generated cationic species in the solvent and other factors. Therefore, it must be noted that the reaction of this study was carried out in an organic solvent, mainly PGME. Furthermore, the composition of solvent was changed with the progress of reaction owing to methanol produced by hydrolysis. Therefore, discussing the reactivity of the base from the pKa value of a particular solvent is difficult. However, TEA has the highest reactivity in PGME than other bases. This may be because TEA has three alkyl chains, which are electron-donating groups, and the NH $(C_2H_5)^{3+}$ generated from TEA has stability in organic solvents owing to its three alkyl chains. SEM images and viscosity measurements showed that small $SiO₂$ nanoparticles were simultaneously generated and interconnected when TEA was used as a basic catalyst.

These results indicate that the structure of the porous $SiO₂$ thin films differed depending on the organic base used. In particular, a fine-structured low-scattering film was obtained using a highly basic catalyst (TEA). However, gelation did not

Fig. 5Viscosity of the reaction mixture containing (a) TEA, (b) DEA , (c) PA, and (d) $NH₃$ as the catalyst to reaction time

proceed when $NH₃$ was used as a basic catalyst. The refractive index of the thin film could be decreased by interlinking small $SiO₂$ nanoparticles using TEA and by growing $SiO₂$ nanoparticles using NH3. In conclusion, TEA is a suitable catalyst for synthesizing porous $SiO₂$ thin films for AR coating.

3.**3**. **Inner and Surface Structure of a Thin Film**

The Structural characteristics of $SiO₂$ PGME TEA (n = 1.17) were investigated. Figure 6 shows the pore distribution measured via positron annihilation spectroscopy. Two peaks were observed at 0.48 nm and 2.4 nm. The peak at 0.48 nm could be attributed to the gap in the siloxane framework [25] and that at 2.4 nm could be ascribed to the presence of pores in $SiO₂$ films.

Fig. 6 Pore size distribution of SiO₂ PGME TEA (n = 1.17) measured using positron annihilation spectroscopy

Figure 7 shows a 3D-TEM image of $SiO₂$ -PGME_TEA. The colored areas represent pores that were detected by image analysis. Several pores were distributed inside the film. Image analysis also revealed the pore distribution, which showed that the pore diameter was in the range of 2–3 nm. This is consistent with the results induced via positron annihilation spectroscopy. Additionally, porosity was calculated to be 65 vol % via image analysis. Considering that the refractive index calculated from the reflectance measurement was $n = 1.17$, the porosity of the film was calculated from the Lorentz–Lorentz formula using the refractive index of $SiO₂$ and air and their volume fractions [26]. The porosity calculated using the refractive index was 62.2 vol %. This result indicates that a 3D-TEM structural analysis was appropriate. Therefore, $SiO₂$ PGME TEA was confirmed to possess abundant pores of diameter 2–3 nm and a high porosity of over 60 vol%. This high porosity was attributed to

the bulky colloidal $SiO₂$ structure grown in the coating liquid. If $SiO₂$ in the coating liquid were mono-dispersed spherical particles, the porosity of porous $SiO₂$ thin films would be 49.4 vol%, as calculated using Structure of NAno Particles (SNAP) simulation [27], [28]. This shows that the $SiO₂$ in the coating liquid possessed a bulky structure formed by connecting small $SiO₂$ nanoparticles. Because bulky $SiO₂$ structures could not be densely packed like mono-dispersed spherical nanoparticles, they formed a highly porous $SiO₂$ thin film.

Fig. 7 3D-TEM image of SiO₂_PGME_TEA The refractive indices of the films were adjusted to $n =$ 1.17. Colored areas were detected pores using image analysis.

The size of the pores in SiO_2 -PGME_TEA (2–3 nm) was smaller than the wavelength of visible light, indicating that $SiO₂$ PGME_TEA can exhibit a low scattering of light [29].

3.**4**. **Enhanced Hydrophobicity of SiO2_PGME_TEA**

The adsorption of moisture from air into porous $SiO₂$ was reported to increase the refractive index [14]. When porous $SiO₂$ is used for AR coating, increasing the refractive index affects the optical properties. Therefore, the Si-OH groups in $SiO₂$ PGME_TEA should be capped by hydrophobic groups. HMDS was used for capping the Si-OH groups because it is commonly used for hydrophobization [30].

In the infrared reflection-absorption spectra (IR-RAS) (Fig. 8) of SiO₂_PGME_TEA and SiO₂_HMDS, an adsorption band at 1250 cm^{-1} was observed in only SiO_2 _HMDS, which was assigned to *ν*(Si-C) [31]. It showed that HMDS was introduced into $SiO₂$ -PGME_TEA.

In addition, the contact angles of $SiO₂$ PGEM_TEA and $SiO₂$ HMDS were measured to be 8.7° and 65°, respectively (Fig. 9). This indicated that $SiO₂$ -PGEM_TEA possessed a hydrophilic surface, whereas $SiO₂$ HMDS possessed a hydrophobic surface. These results revealed that HMDS successfully capped the Si-OH group and increased the

Fig. 9 Contact angle measurement of SiO₂_PGME_TEA (a) before and (b) after HMDS treatment

hydrophobicity of $SiO₂$ -PGME_TEA.

The refractive indices of SiO_2 -PGME_TEA and SiO_2 HMDS are listed in Table 2. The refractive index of $SiO₂$ HMDS was higher than that of $SiO₂$ -PGME_TEA. It probably indicated that HMDS was introduced into the pores of $SiO₂$ -PGME_TEA. Moreover, the changes in refractive indices after keeping the films at 24°C and 35% relative humidity for 7 d were compared. The increase in the refractive index of $SiO₂$ -HMDS was smaller than that of $SiO₂$ PGME_TEA for 7 d.

Table 2 Refractive indices of SiO₂ PGME TEA and SiO₂ HMDS on 0, and 7 d

| | | | n on day $0/$ - n on day $7/$ - Increase in n after $7 d/$ - |
|-----------------|-------|-------|--|
| $SiO2$ PGME TEA | 1.170 | 1.212 | 0.042 |
| $SiO2$ HMDS | 1 197 | 1.209 | 0.012 |

Hence, the HMDS treatment prevented an increase in the refractive index of the porous $SiO₂$ thin films via the capping of the Si-OH groups.

4 Conclusion

Porous $SiO₂$ thin films having low refractive indices were successfully prepared via a simple sol-gel method. The choice of solvent and basic catalyst is a key factor for controlling the reactivity of the coating liquid and forming a smooth film that exhibits low scattering. The porous $SiO₂$ thin film fabricated in this study could be used as a broadband AR coating with stacked undercoating and as a lens and sensor in various optical devices.

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